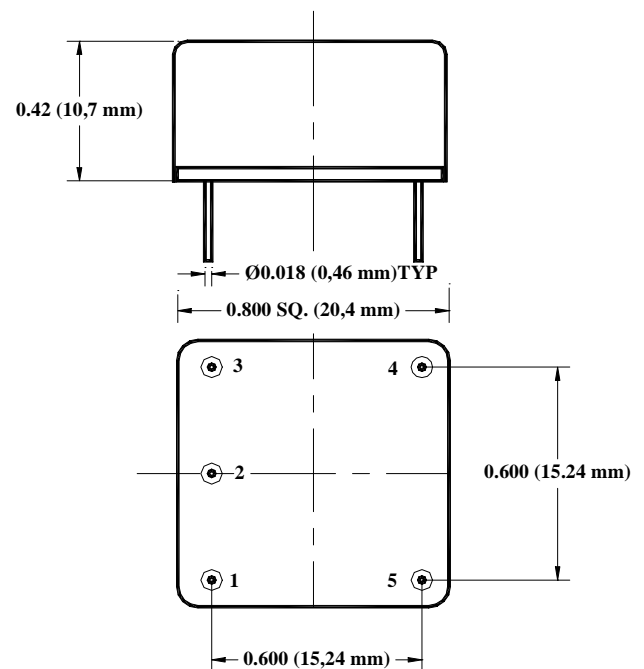
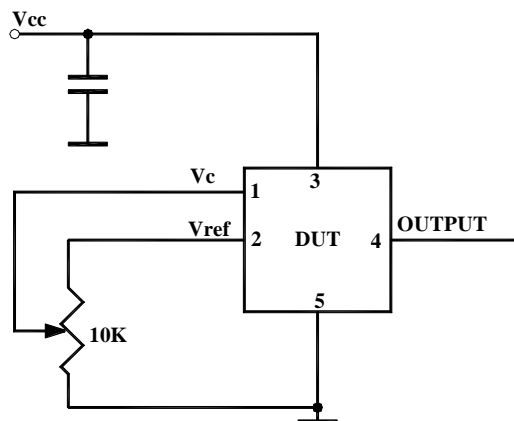


OD-X8HXXXXX**Precision SC-cut OCXO in 20x20 mm Through Hole Package****Product Data Sheet****Features**

- SC-cut crystal
- High Stability (up to $\pm 5 \times 10^{-9}$)
- Low Aging (5×10^{-10} /day, 5×10^{-8} /year)
- Low Phase Noise (-160 dBc/Hz, TYP, floor)
- Sine Wave or HCMOS/TTL output
- 4.8 MHz to 160 MHz Frequencies Available

Applications

- Telecommunication Systems
- Data Communications
- GPS
- Instrumentation



OD-X8HXXXX Series

Parameter	Symb	Condition	Min	Typ	Max	Unit	Note
Absolute Maximum Ratings							
Input Break Down Voltage	V _{cc}		-0.5		13.0	V	
Storage temper.	T _s		-40		85	°C	
Control Voltage	V _c		-1		9	V	

Electrical

Frequency	F		4.8	10.000	160	MHz	1*
Frequency stability	ΔF/F	vs. Temp.		±10		ppb	See chart below
		vs. Supply		1	2	ppb/V	
Aging		per day per year		5E-10 1E-7			after 30 days 5E-8 available2*
Allan Variance		.1s to 10s		1E-11			
SSB Phase Noise		1 Hz		-90		dBc/Hz	3*
		10 Hz		-120			
		100 Hz		-150			
		1 KHz		-153			
		10 KHz		-160			
Retrace		After 30 minutes			±10	ppb	
G-sensitivity		worst direction			±1.0	ppb/G	
Input Voltage	V _{cc}		4.75 3.15 11.4	5.0 3.3 12.0	5.25 3.45 12.6	V	See chart below to specify
Power consumption	P	steady state, 25°C steady state, -30°C start-up @ -30°C		0.8 1.5 2.5	1.2 3.2	W	Standard Operating Temperature, for Op Temp. 85 °C ad 20%
Spectral Purity		Subharmonics Spurious Harmonics/Sine		-50 -35	-45 -30	dBc	At Higher Frequencies
Load		10KOhm//15pF (HCMOS/TTL), 50 Ohm (Sinewave)					
Warm-up time	τ	to 0.1ppm accuracy		3	5	minutes	3 min. at 12V
Output Waveform		3.3V HCMOS/TTL compatible or Sinewave (+7±3) dBm					
Control voltage	V _c		0		4.0	V	
Pull range		from nominal F	±0.5	±1		ppm	
Deviation slope		Monotonic, posit		0.4		ppm/V	
Setability	V _{c0}	@25°C, F _{nom} .	1.0	2.0	3.0	V	

All parameters for 10 MHz

Environmental and Mechanical

Operating temp. range	-30°C to 70°C Standard, Other options – see chart below
Mechanical Shock	Per MIL-STD-202, 30G, 11ms
Vibration	Per MIL-STD-202, 5G to 2000 Hz
Soldering Conditions	260°C for 10s Max leads only

Electrical Connections

Pin Out	Pin #1-V _c ; Pin#2 – V _{ref} ; Pin #3 – V _{cc} ; Pin #4- Output ; Pin #5- GND;
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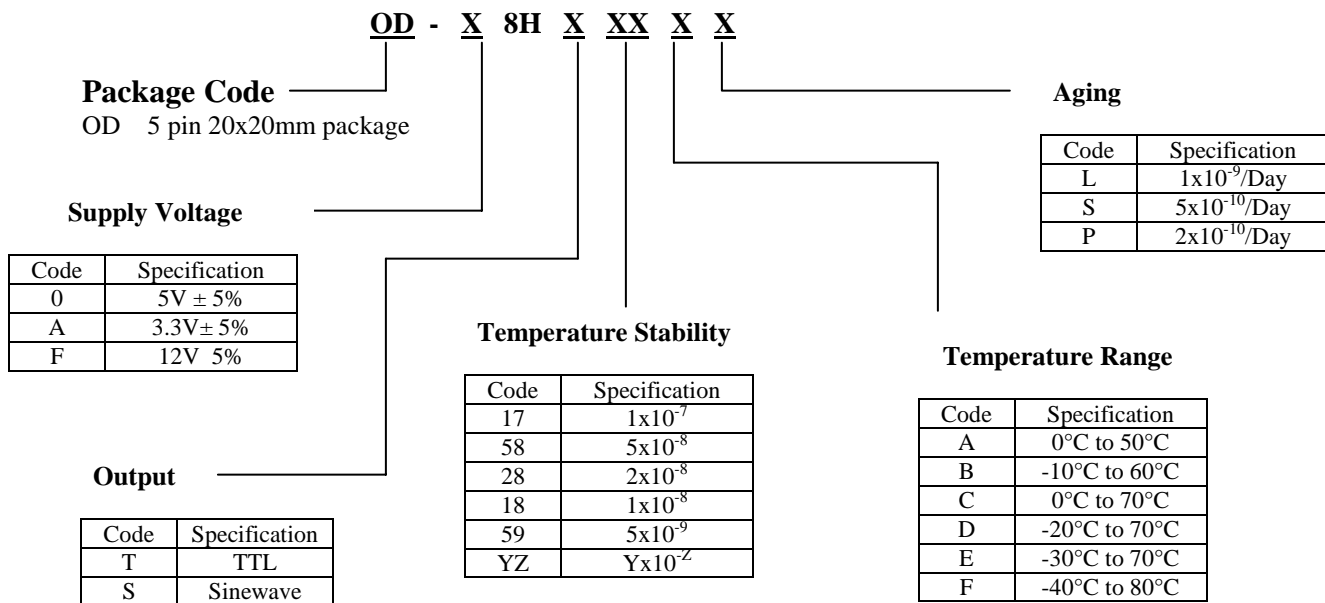
Notes: 1* Higher frequencies can be achieved either by using higher frequency crystals or by low noise analog harmonic multiplication. Both methods have advantages and drawbacks. If lowest possible phase noise on the noise floor is most important – high frequency crystal will be used. If phase noise close to the carrier and aging are more important – multiplication will be used. Please consult factory for your specific requirement.

2* Aging rate is usually proportional to the operating frequency, unless higher frequency is achieved by multiplication. Keep it in mind while specifying aging.

3* Phase noise deteriorates with frequencies going higher. If analog multiplication is used to achieve higher frequency the phase noise roughly follows the formula of additional 20LogN, where N is a multiplication factor across entire frequency offset range. If higher frequency is achieved by using higher frequency crystal phase noise close to the carrier deteriorates due to the lower Q of the crystal and is usually worse, compared to multiplied solution. On the noise floor, however it remains more or less the same. This design usually starts utilizing multiplication techniques in the range of 25 MHz to 35 MHz.

OD-X8HXXXXX Series

Creating a Part Number



Not all combinations are available. Consult Factory.